

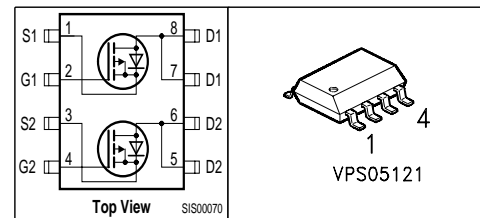
OptiMOS[®]-P Small-Signal-Transistor

Feature

- Dual P-Channel
- Enhancement mode
- Logic Level
- 150°C operating temperature
- Avalanche rated
- dv/dt rated

Product Summary

| | | |
|--------------|------|------------|
| V_{DS} | -30 | V |
| $R_{DS(on)}$ | 21 | m Ω |
| I_D | -8.2 | A |



| Type | Package | Ordering Code |
|---------|---------|---------------|
| BSO303P | SO 8 | Q67042-S4010 |

Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|---|--------------------|--------------|-------------------|
| Continuous drain current $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$ | I_D | -8.2 -6.6 | A |
| Pulsed drain current $T_A=25^\circ\text{C}$ | $I_D \text{ puls}$ | -32.4 | |
| Avalanche energy, single pulse $I_D=-8.2\text{ A}$, $V_{DD}=-25\text{V}$, $R_{GS}=25\Omega$ | E_{AS} | 97 | mJ |
| Reverse diode dv/dt $I_S=-8.2\text{A}$, $V_{DS}=-24\text{V}$, $di/dt=200\text{A}/\mu\text{s}$, $T_{jmax}=150^\circ\text{C}$ | dv/dt | -6 | kV/ μs |
| Gate source voltage | V_{GS} | ± 20 | V |
| Power dissipation $T_A=25^\circ\text{C}$ | P_{tot} | 2 | W |
| Operating and storage temperature | T_j, T_{stg} | -55... +150 | $^\circ\text{C}$ |
| IEC climatic category; DIN IEC 68-1 | | 55/150/56 | |

Thermal Characteristics

| Parameter | Symbol | Values | | | Unit |
|---|------------|--------|------|-------------|------|
| | | min. | typ. | max. | |
| Characteristics | | | | | |
| Thermal resistance, junction - soldering point | R_{thJS} | - | - | 50 | K/W |
| SMD version, device on PCB: | R_{thJA} | | | | |
| @ min. footprint, $t < 10s$ @ 6 cm ² cooling area ¹⁾ | | - | - | 110 62.5 | |

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|---------------|--------|------|------|------------|
| | | min. | typ. | max. | |
| Static Characteristics | | | | | |
| Drain-source breakdown voltage $V_{GS}=0, I_D=-250\mu A$ | $V_{(BR)DSS}$ | -30 | - | - | V |
| Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-100\mu A$ | $V_{GS(th)}$ | -1 | -1.5 | -2 | |
| Zero gate voltage drain current $V_{DS}=-30V, V_{GS}=0, T_j=25^\circ C$ $V_{DS}=-30V, V_{GS}=0, T_j=150^\circ C$ | I_{DSS} | - | -0.1 | -1 | μA |
| | | - | -10 | -100 | |
| Gate-source leakage current $V_{GS}=-20V, V_{DS}=0$ | I_{GSS} | - | -10 | -100 | nA |
| Drain-source on-state resistance $V_{GS}=-4.5V, I_D=-6.6A$ | $R_{DS(on)}$ | - | 26 | 32 | m Ω |
| Drain-source on-state resistance $V_{GS}=-10V, I_D=-8.2A$ | $R_{DS(on)}$ | - | 18 | 21 | |

¹⁾Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air; $t \leq 10$ sec.

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic Characteristics

| | | | | | | |
|------------------------------|--------------|--|----|------|------|----|
| Transconductance | g_{fs} | $ V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ $I_D = -6.6A$ | 11 | 22 | - | S |
| Input capacitance | C_{iss} | $V_{GS} = 0, V_{DS} = -25V,$ $f = 1MHz$ | - | 1761 | - | pF |
| Output capacitance | C_{oss} | | - | 495 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 410 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = -15V, V_{GS} = -10V,$ $I_D = -1A, R_G = 6\Omega$ | - | 10.6 | 15.9 | ns |
| Rise time | t_r | | - | 12.9 | 19.3 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 55.4 | 83.1 | |
| Fall time | t_f | | - | 39.3 | 59 | |

Gate Charge Characteristics

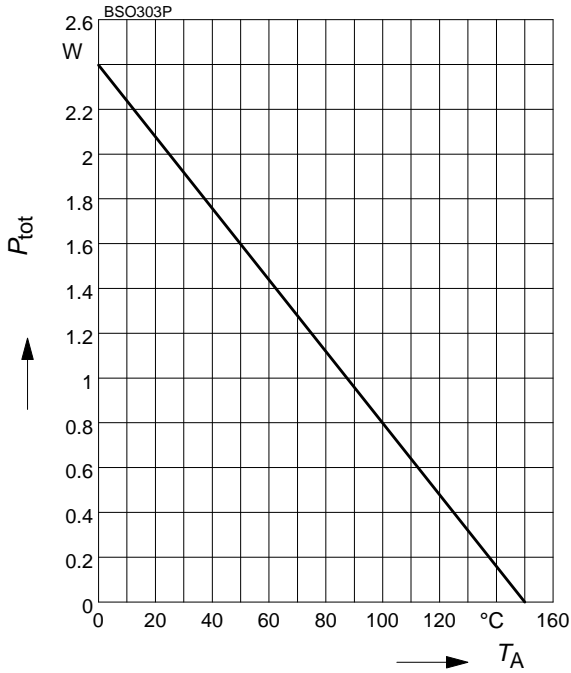
| | | | | | | |
|-----------------------|-----------------|--|---|-------|-------|----|
| Gate to source charge | Q_{gs} | $V_{DD} = -24V, I_D = -8.2A$ | - | -4.25 | -6.4 | nC |
| Gate to drain charge | Q_{gd} | | - | -15.2 | -23 | |
| Gate charge total | Q_g | $V_{DD} = -24V, I_D = -8.2A,$ $V_{GS} = 0 \text{ to } -10V$ | - | -48.3 | -72.5 | |
| Gate plateau voltage | $V_{(plateau)}$ | $V_{DD} = -24V, I_D = -8.2A$ | - | -2.4 | - | V |

Reverse Diode

| | | | | | | |
|--|----------|--|---|-------|-------|----|
| Inverse diode continuous forward current | I_S | $T_A = 25\text{ °C}$ | - | - | -2.2 | A |
| Inverse diode direct current, pulsed | I_{SM} | | - | - | -32.4 | |
| Inverse diode forward voltage | V_{SD} | $V_{GS} = 0, I_F = I_D $ | - | -0.88 | -1.32 | |
| Reverse recovery time | t_{rr} | $V_R = -15V, I_F = I_D ,$ $dI_F/dt = 100A/\mu s$ | - | 24.4 | 36.6 | ns |
| Reverse recovery charge | Q_{rr} | | - | 12.8 | 19.2 | nC |

1 Power dissipation

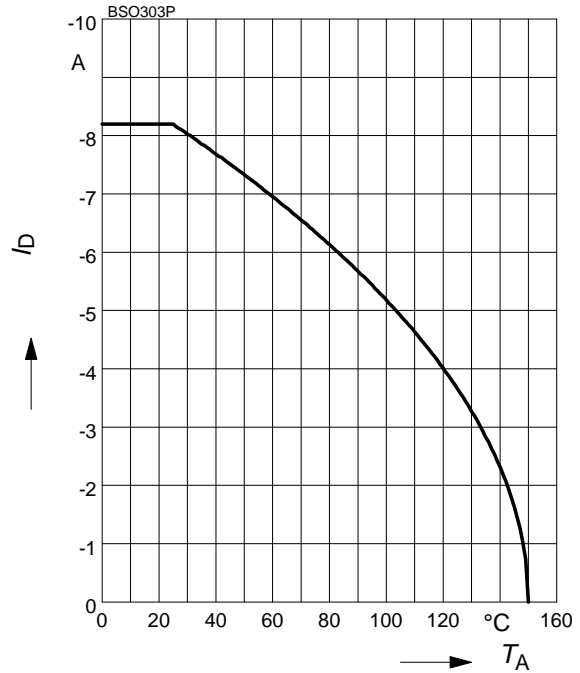
$$P_{tot} = f(T_A)$$



2 Drain current

$$I_D = f(T_A)$$

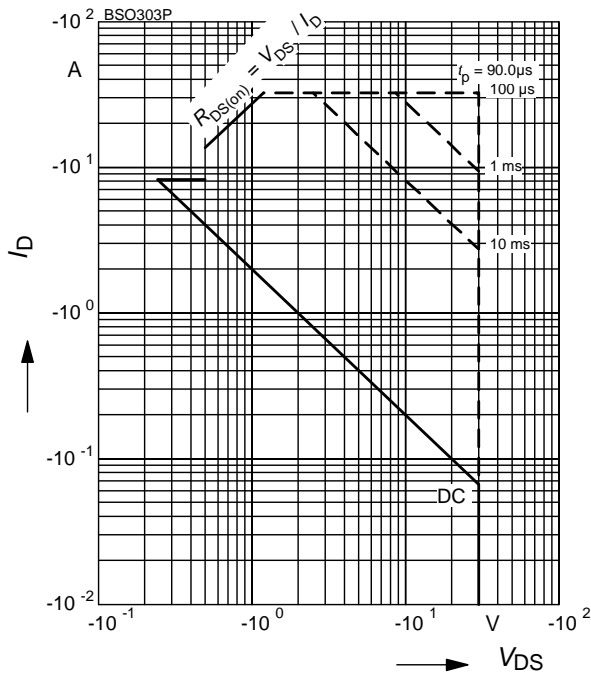
parameter: $|V_{GS}| \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

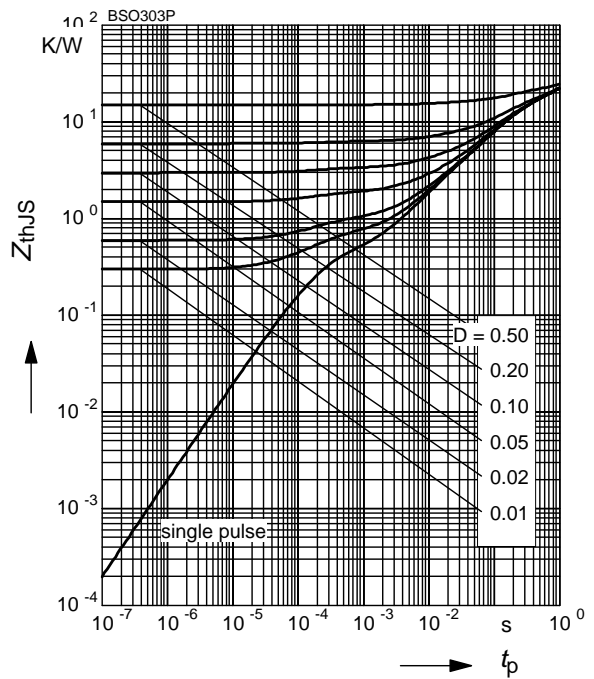
parameter: $D = 0, T_A = 25 \text{ °C}$



4 Transient thermal impedance

$$Z_{thJS} = f(t_p)$$

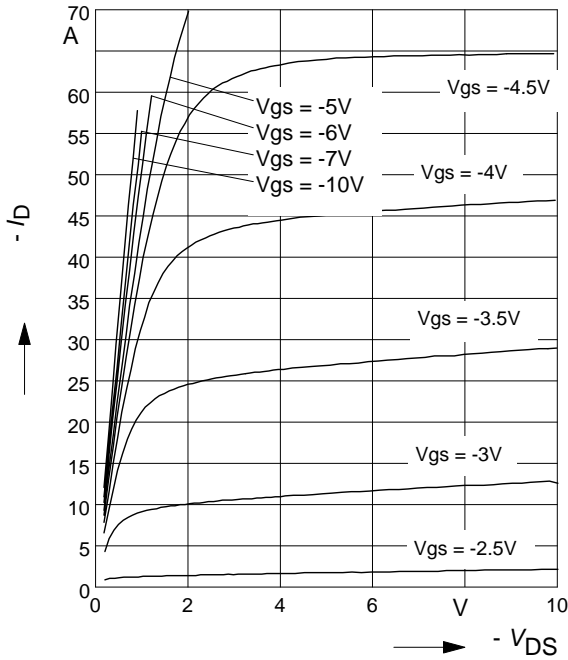
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j=25^\circ\text{C}$

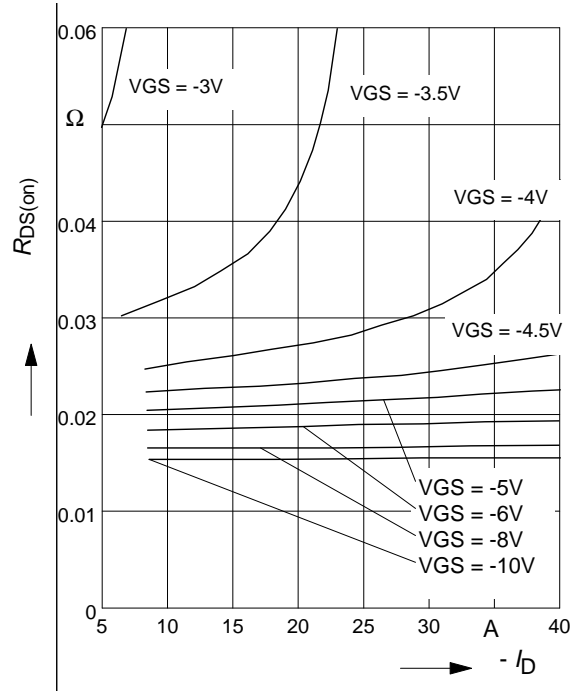
parameter: $t_p = 80 \mu\text{s}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

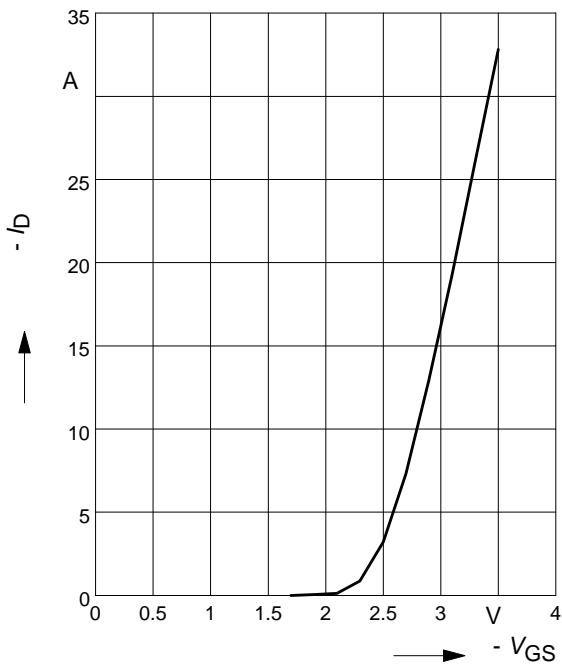
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

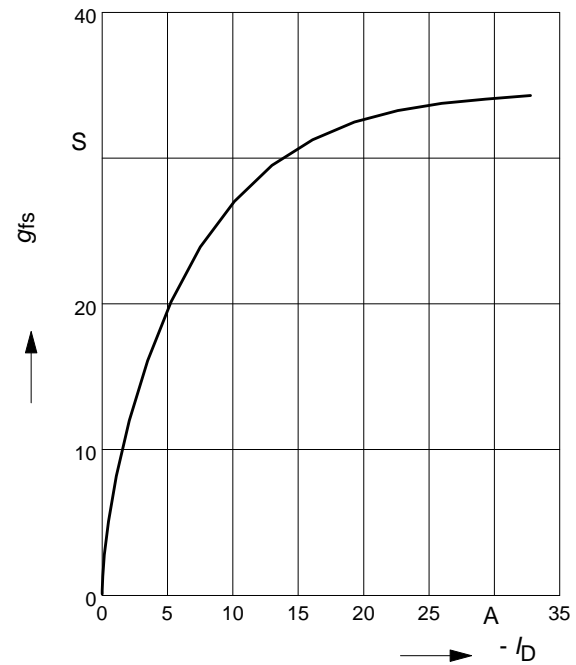
parameter: $t_p = 80 \mu\text{s}$



8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j=25^\circ\text{C}$

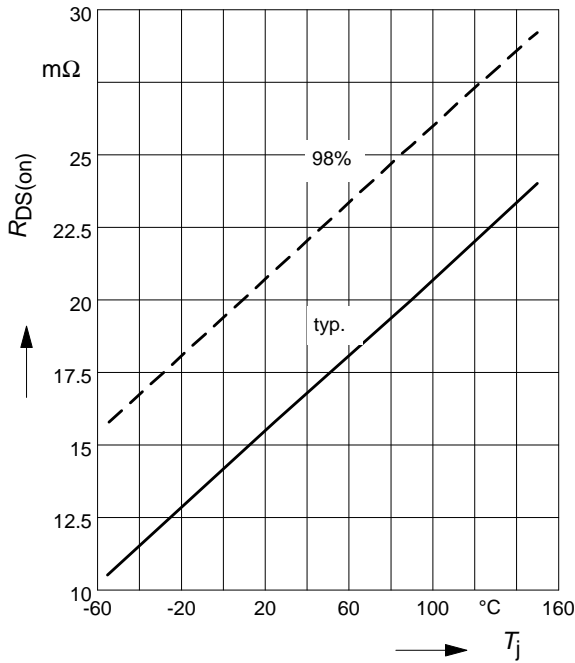
parameter: $t_p = 80 \mu\text{s}$



9 Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

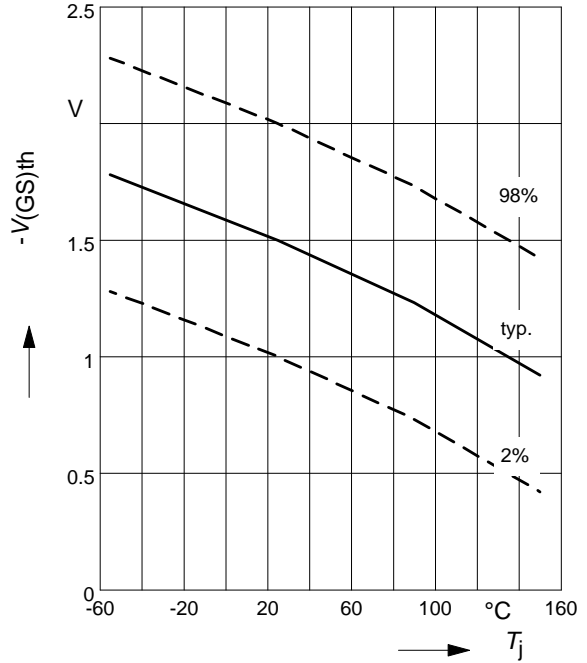
parameter: $I_D = -8.2 \text{ A}$, $V_{GS} = -10 \text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

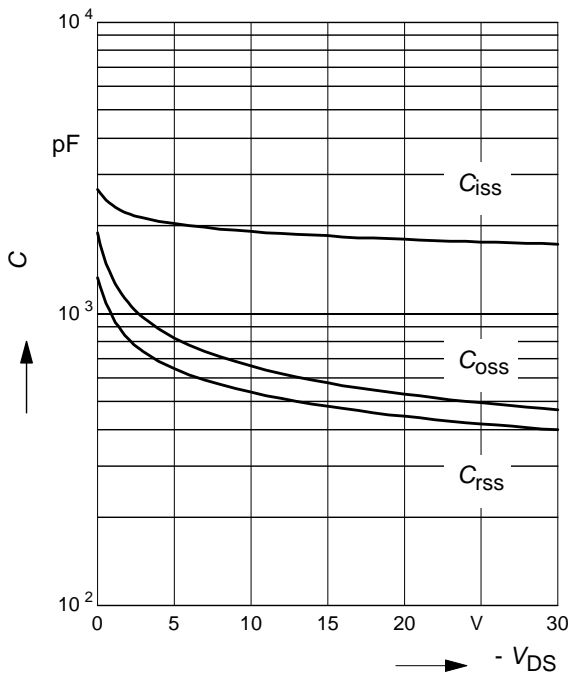
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

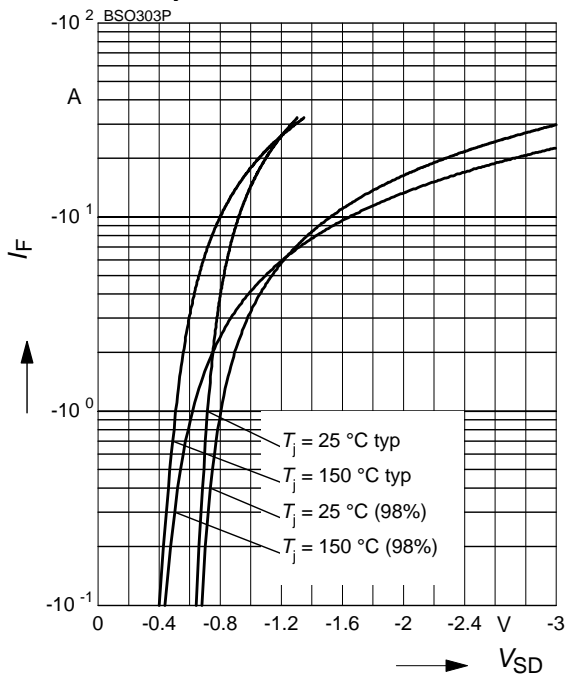
parameter: $V_{GS}=0$, $f=1 \text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

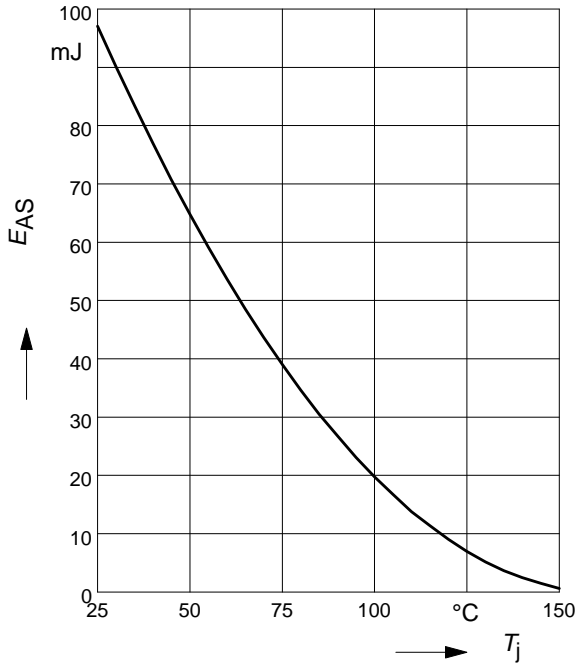
parameter: T_j , $t_p = 80 \mu\text{s}$



13 Typ. avalanche energy

$E_{AS} = f(T_j)$, par.: $I_D = -8.2\text{ A}$

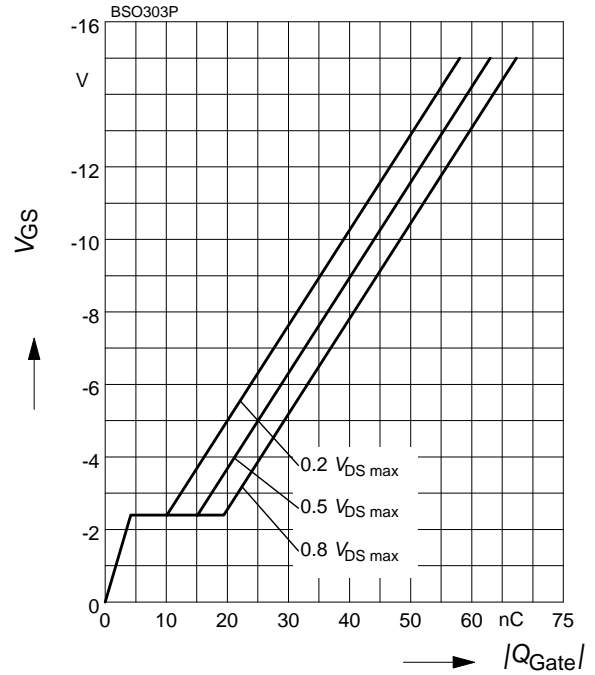
$V_{DD} = -25\text{ V}$, $R_{GS} = 25\ \Omega$



14 Typ. gate charge

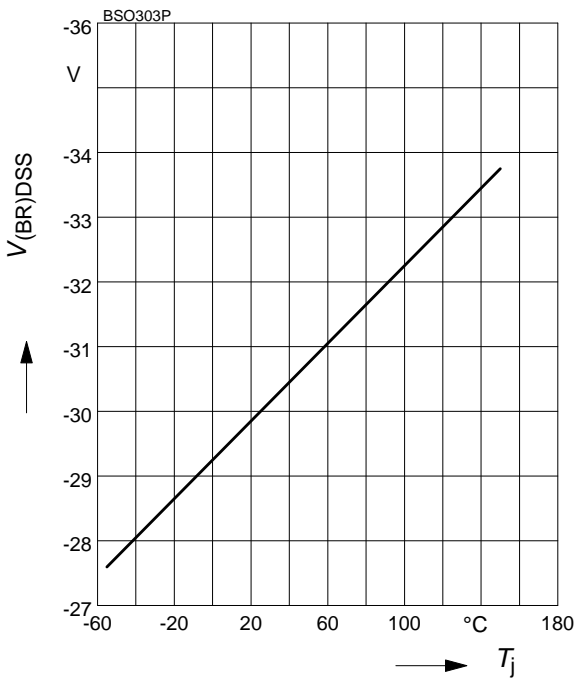
$V_{GS} = f(Q_{Gate})$

parameter: $I_D = -8.2\text{ A}$ pulsed



15 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



Published by
Infineon Technologies AG,
Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München
© Infineon Technologies AG 1999
All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.